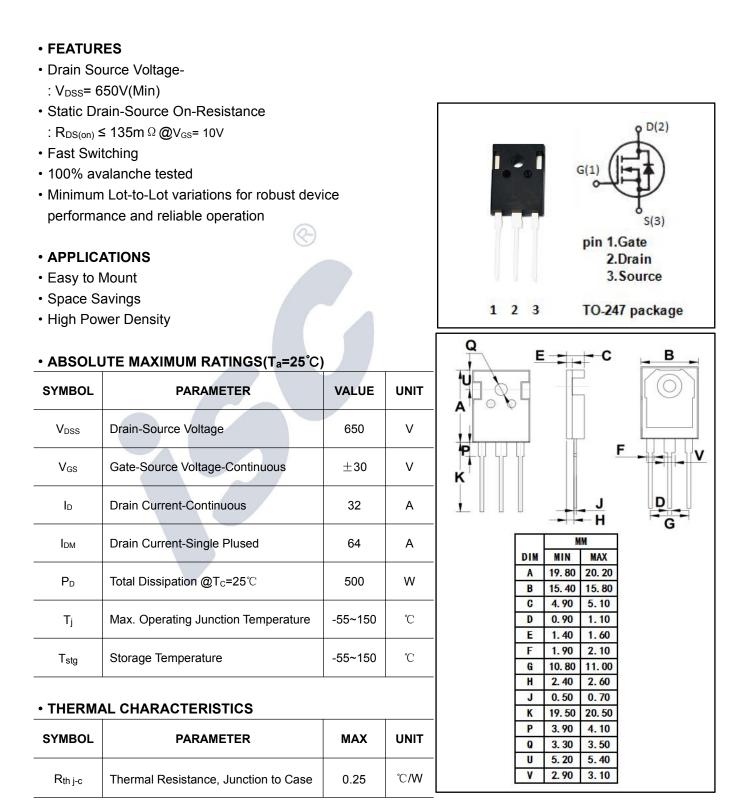


#### **INCHANGE SEMICONDUCTOR**

## isc N-Channel MOSFET Transistor

# IXTH32N65X



isc website: <u>www.iscsemi.com</u>



# isc N-Channel MOSFET Transistor

## IXTH32N65X

#### • ELECTRICAL CHARACTERISTICS

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 250uA	650			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}$ = $V_{GS}$ ; $I_D$ = 250uA	3		5.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 16A			135	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0 V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0;TJ=125℃			5 50	μA
V <sub>SD</sub>	Diode Forward On-voltage	I <sub>F</sub> = 32A ;V <sub>GS</sub> = 0			1.4	V

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